Unit: mm

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOSIII)

# SSM6J26FE

## **High Speed Switching Applications**

• Optimum for high-density mounting in small packages

• Low on-resistance:  $R_{on} = 230 \text{m}\Omega \text{ (max) (@V_{GS} = -4 V)}$ 

 $R_{on} = 330 m\Omega \text{ (max) (@V_{GS} = -2.5 V)}$ 

 $R_{on} = 980 m\Omega \text{ (max) } (@V_{GS} = -1.8 \text{ V})$ 

## Absolute Maximum Ratings (Ta = 25°C)

| Characteristics           |       | Symbol                     | Rating     | Unit         |  |
|---------------------------|-------|----------------------------|------------|--------------|--|
| Drain-Source voltage      |       | $V_{DS}$                   | -20        | V            |  |
| Gate-Source voltage       |       | $V_{GSS}$                  | ± 8        | $(\sqrt{y})$ |  |
| Drain current             | DC    | ΙD                         | -0.5       | A            |  |
|                           | Pulse | I <sub>DP</sub>            | -1.5       |              |  |
| Drain power dissipation   |       | P <sub>D</sub><br>(Note 1) | 500        | → mW         |  |
| Channel temperature       |       | T <sub>ch</sub>            | 150        | °C           |  |
| Storage temperature range |       | T <sub>stg</sub>           | -55 to 150 | °C           |  |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

1.6±0.05 1.2±0.05 1.2±0.05 1.2±0.05 1.2±0.05 1.2±0.05 4 90.0+20 1.2,5,6 :Drain 3.:Gate 4 :Source JEDEC —

JEITA —

TOSHIBA 2-2N1A

Weight: 3.0 mg (typ.)

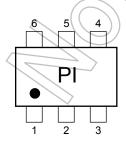
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

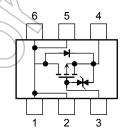
Note 1: Mounted on FR4 board.

 $(25.4 \text{ mm} \times 25.4 \text{ mm} \times 1.6 \text{ t}, \text{ Cu Pad: } 645 \text{ mm}^2)$ 

#### Marking

# **Equivalent Circuit (top view)**





#### **Handling Precaution**

When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

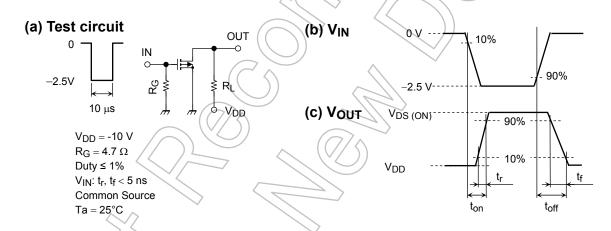
Start of commercial production 2004-03

## **Electrical Characteristics (Ta = 25°C)**

| Chara                          | acteristics   | Symbol                                       | Test Condition   | Min           | Тур. | Max        | Unit |  |
|--------------------------------|---------------|--|--|---------------|------|------------|------|--|
| Gate leakage cur               | rent          | I <sub>GSS</sub>                             | $I_{GSS}$ $V_{GS} = \pm 8 \text{ V}, V_{DS} = 0$           |               | _    | ±1         | μΑ   |  |
| Drain-Source breakdown voltage | V (BR) DSS    | $I_D = -1 \text{ mA}, V_{GS} = 0$            | -20  | _             | _    | ٧          |      |  |
|                                | V (BR) DSX    | $I_D = -1 \text{ mA}, V_{GS} = +8 \text{ V}$ | -12  | _             | _    |            |      |  |
| Drain cut-off curre            | ent           | I <sub>DSS</sub>                             | V <sub>DS</sub> = -20 V, V <sub>GS</sub> = 0               |               | _    | -1         | μΑ   |  |
| Gate threshold vo              | oltage        | V <sub>th</sub>                              | $V_{DS} = -3 \text{ V}, I_{D} = -0.1 \text{ mA}$           | -0.5          | ))^_ | -1.1       | V    |  |
| Forward transfer               | admittance    | Y <sub>fs</sub>                              | $V_{DS} = -3 \text{ V}, I_D = -0.25 \text{ A}$ (Note2)     | 0.8           | 1.7  | _          | S    |  |
| Drain-Source on-resistance     |               | R <sub>DS</sub> (ON)                         | I <sub>D</sub> = -0.25 A, V <sub>GS</sub> = -4 V (Note2)   | $\mathcal{C}$ | 200  | 230        | mΩ   |  |
|                                |               |  | I <sub>D</sub> = -0.25 A, V <sub>GS</sub> = -2.5 V (Note2) |               | 260  | 330        |      |  |
|                                |               |  | I <sub>D</sub> = -0.25 A, V <sub>GS</sub> = -1.8 V (Note2) | _             | 400  | 980        |      |  |
| Input capacitance              | •             | C <sub>iss</sub>                             | V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0, f = 1 MHz    | _             | 250  |            | pF   |  |
| Reverse transfer               | capacitance   | C <sub>rss</sub>                             | V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0, f = 1 MHz    |               | 35   | $\searrow$ | pF   |  |
| Output capacitan               | ce            | C <sub>oss</sub>                             | V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0, f = 1 MHz    | -6            | 45   | > —        | pF   |  |
| Switching time                 | Turn-on time  | t <sub>on</sub>                              | V <sub>DD</sub> = -10 V, I <sub>D</sub> = -0.25 A,         | (             | 14   | ) —        | ns   |  |
|                                | Turn-off time | t <sub>off</sub>                             | $V_{GS} = 0$ to -2.5 V, $R_G = 4.7 \Omega$                 | 1             | 15   | _          |      |  |

Note2: Pulse test

# **Switching Time Test Circuit**

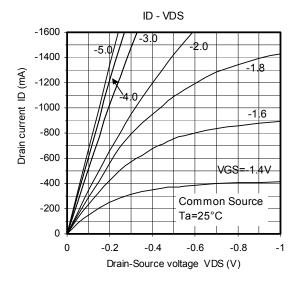


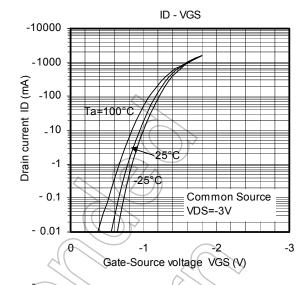
#### **Precaution**

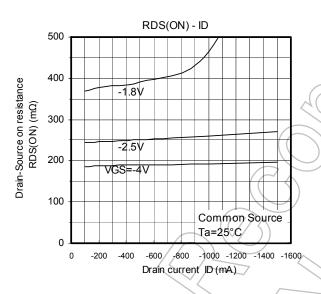
 $V_{th}$  can be expressed as the voltage between gate and source when the low operating current value is  $I_D$  = \_100  $\mu$ A for this product. For normal switching operation,  $V_{GS}$  (on) requires a higher voltage than  $V_{th}$  and  $V_{GS}$  (off) requires a lower voltage than  $V_{th}$ .

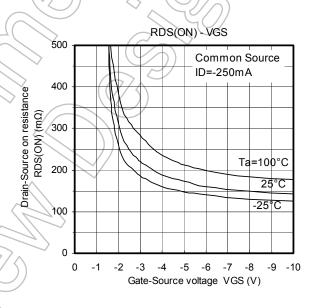
(The relationship can be established as follows:  $V_{GS (off)} < V_{th} < V_{GS (on)}$ )

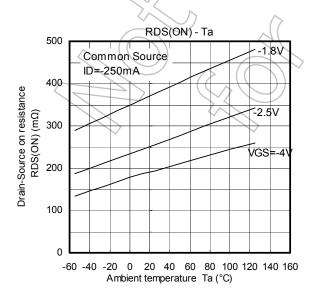
Please take this into consideration when using the device.

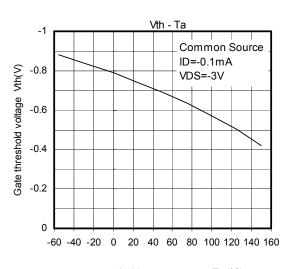






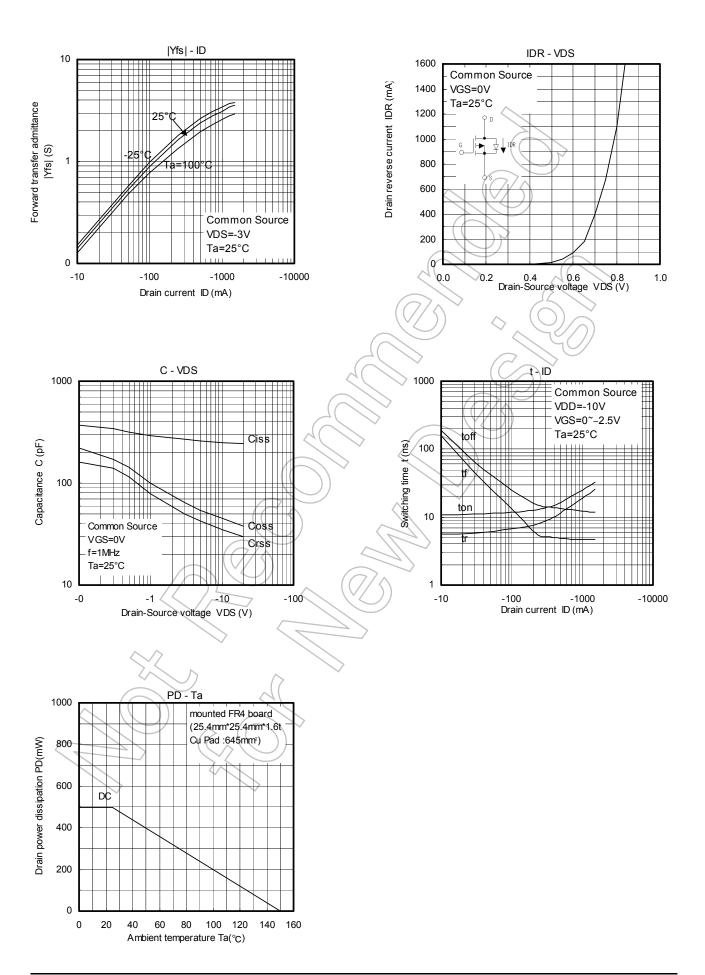






Ambient temperature Ta (°C)

3 2014-03-01



4 2014-03-01

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